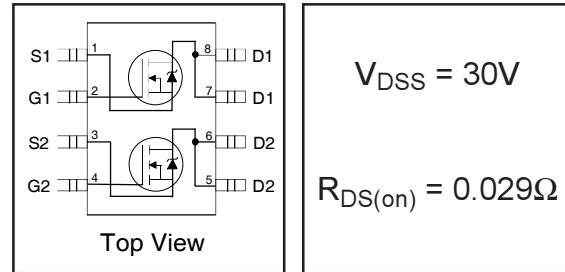


IRF7313QPbF

HEXFET® Power MOSFET

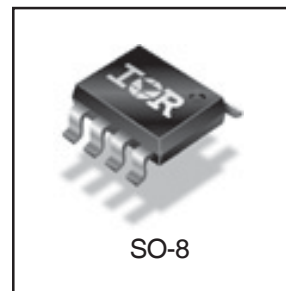
- Advanced Process Technology
- Ultra Low On-Resistance
- Dual N-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- 150°C Operating Temperature
- Lead-Free



Description

These HEXFET® Power MOSFET's in a Dual SO-8 package utilize the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of these HEXFET Power MOSFET's are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These benefits combine to make this design an extremely efficient and reliable device for use in a wide variety of applications.

The efficient SO-8 package provides enhanced thermal characteristics and dual MOSFET die capability making it ideal in a variety of power applications. This dual, surface mount SO-8 can dramatically reduce board space and is also available in Tape & Reel.



Absolute Maximum Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)

	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^①	I_D	$T_A = 25^\circ C$	6.5
		$T_A = 70^\circ C$	5.2
Pulsed Drain Current	I_{DM}	30	A
Continuous Source Current (Diode Conduction)	I_S	2.5	
Maximum Power Dissipation ^②	P_D	$T_A = 25^\circ C$	2.0
		$T_A = 70^\circ C$	1.3
Single Pulse Avalanche Energy ^②	E_{AS}	82	mJ
Avalanche Current	I_{AR}	4.0	A
Repetitive Avalanche Energy	E_{AR}	0.20	mJ
Peak Diode Recovery dv/dt ^③	dv/dt	5.8	V/ ns
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to + 150	$^\circ C$

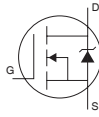
Thermal Resistance Ratings

Parameter	Symbol	Limit	Units
Maximum Junction-to-Ambient ^④	$R_{\theta JA}$	62.5	$^\circ C/W$

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.022	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	0.023	0.029	Ω	V _{GS} = 10V, I _D = 5.8A ④
		—	0.032	0.046		V _{GS} = 4.5V, I _D = 4.7A ④
V _{GS(th)}	Gate Threshold Voltage	1.0	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	—	14	—	S	V _{DS} = 15V, I _D = 5.8A
I _{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V _{DS} = 24V, V _{GS} = 0V
		—	—	25		V _{DS} = 24V, V _{GS} = 0V, T _J = 55°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	22	33	nC	I _D = 5.8A
Q _{gs}	Gate-to-Source Charge	—	2.6	3.9		V _{DS} = 15V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	6.4	9.6		V _{GS} = 10V, See Fig. 10 ④
t _{d(on)}	Turn-On Delay Time	—	8.1	12	ns	V _{DD} = 15V
t _r	Rise Time	—	8.9	13		I _D = 1.0A
t _{d(off)}	Turn-Off Delay Time	—	26	39		R _G = 6.0Ω
t _f	Fall Time	—	17	26		R _D = 15Ω ④
C _{iss}	Input Capacitance	—	650	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	320	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	130	—		f = 1.0MHz, See Fig. 9

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	30		
V _{SD}	Diode Forward Voltage	—	0.78	1.0	V	T _J = 25°C, I _S = 1.7A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	45	68	ns	T _J = 25°C, I _F = 1.7A
Q _{rr}	Reverse Recovery Charge	—	58	87	nC	di/dt = 100A/μs ③

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting T_J = 25°C, L = 10mH
R_G = 25Ω, I_{AS} = 4.0A.
- ③ I_{SD} ≤ 4.0A, di/dt ≤ 74A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Surface mounted on FR-4 board, t ≤ 10sec.

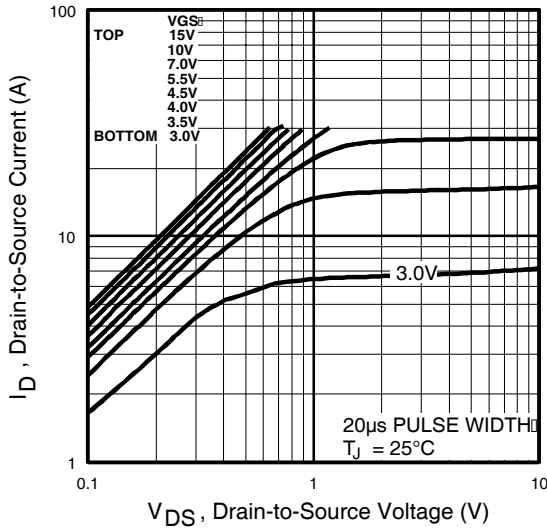


Fig 1. Typical Output Characteristics

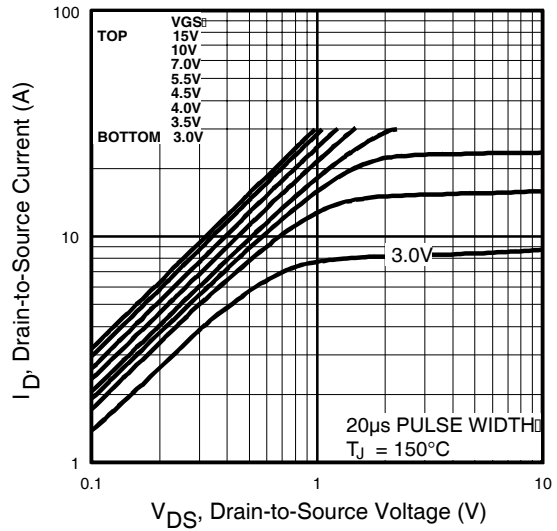


Fig 2. Typical Output Characteristics

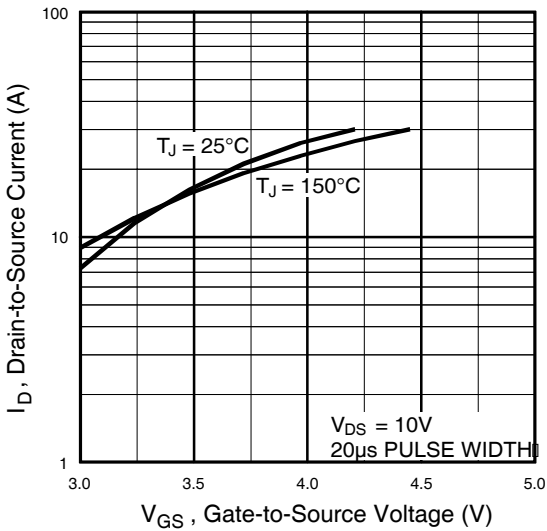


Fig 3. Typical Transfer Characteristics

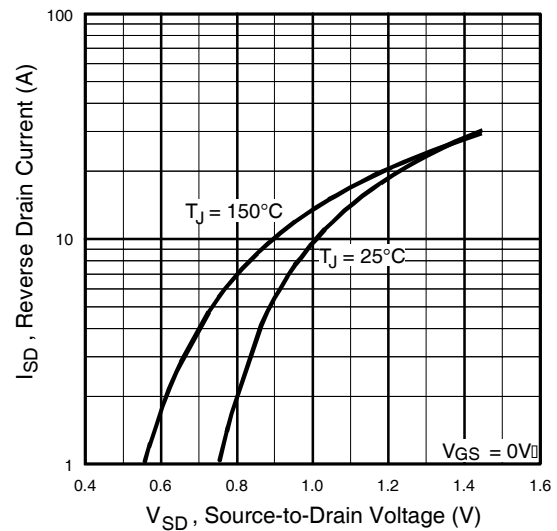


Fig 4. Typical Source-Drain Diode Forward Voltage

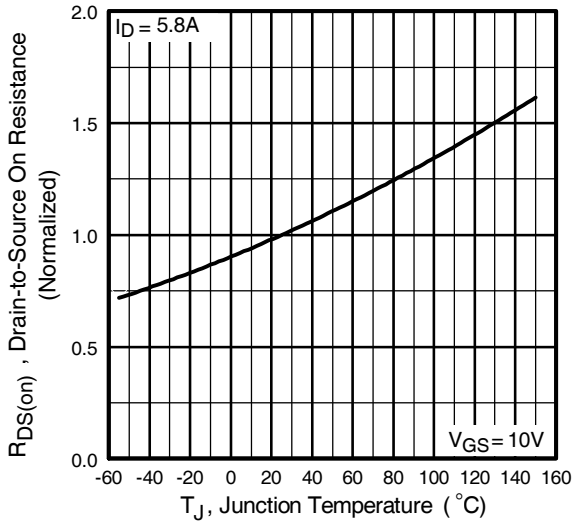


Fig 5. Normalized On-Resistance Vs. Temperature

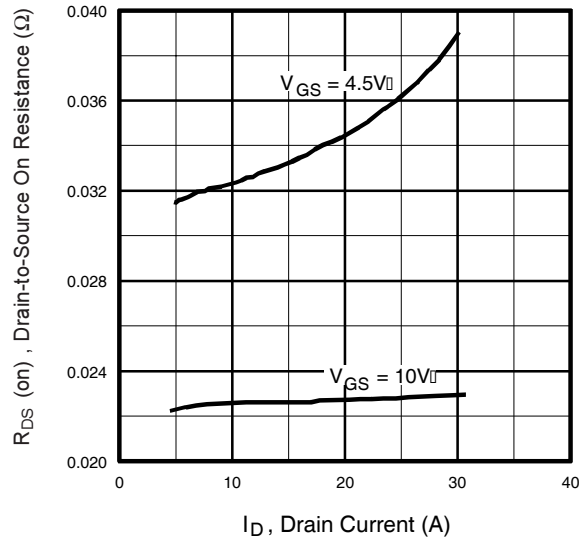


Fig 6. Typical On-Resistance Vs. Drain Current

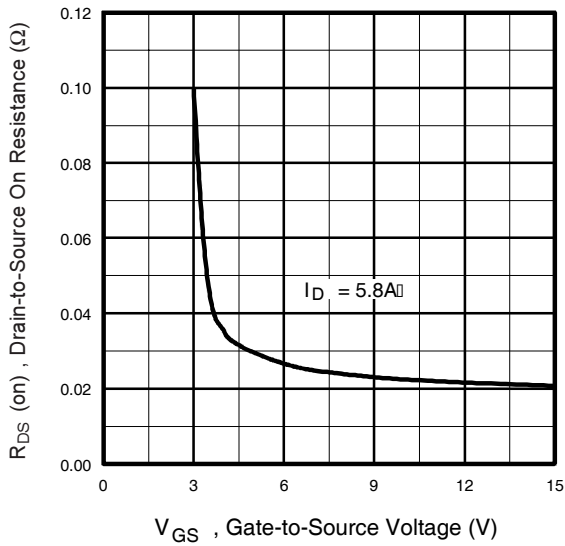


Fig 7. Typical On-Resistance Vs. Gate Voltage

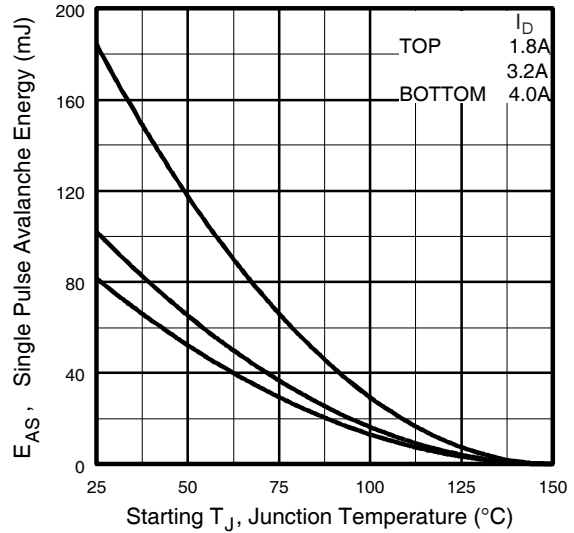


Fig 8. Maximum Avalanche Energy Vs. Drain Current

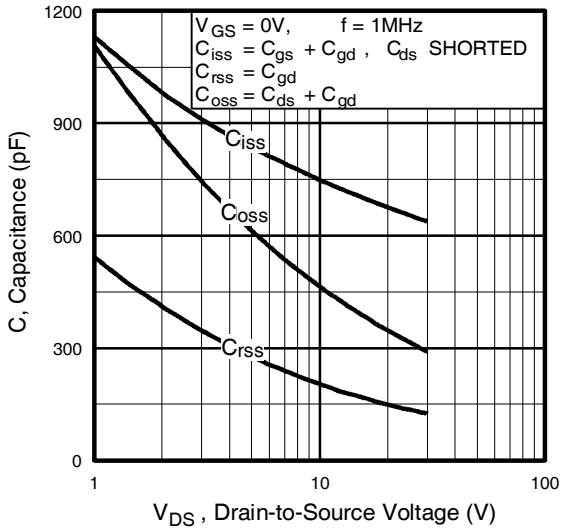


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

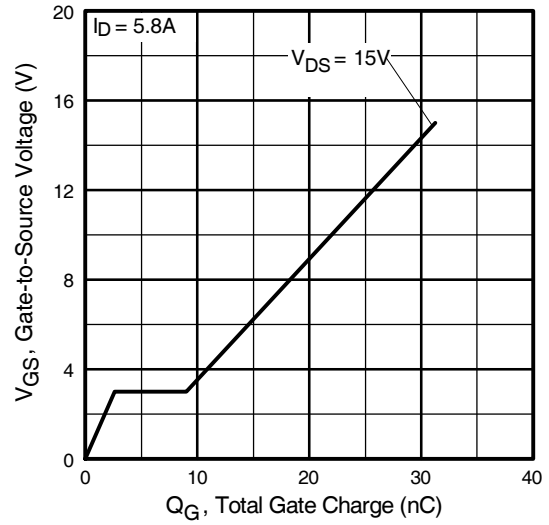


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

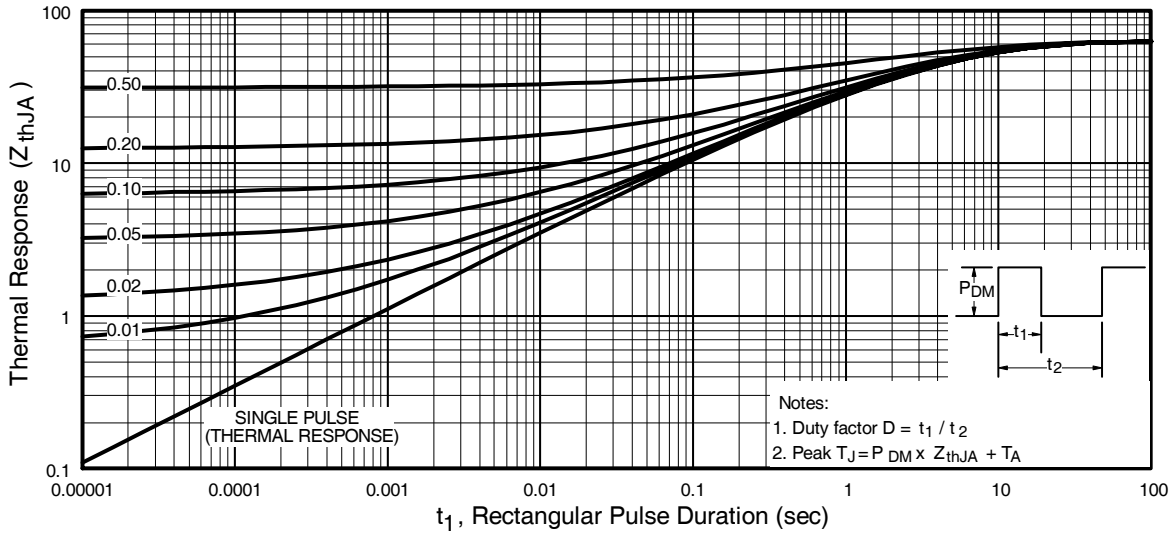


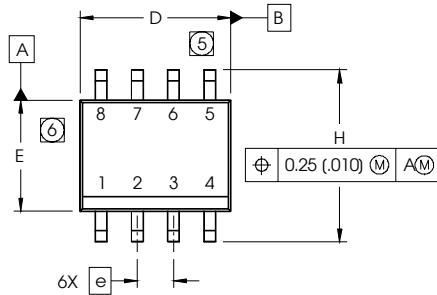
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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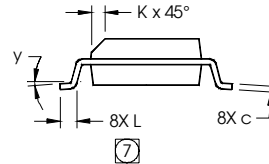
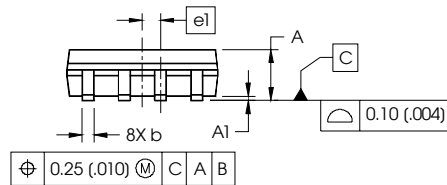
International
IR Rectifier

SO-8 Package Outline

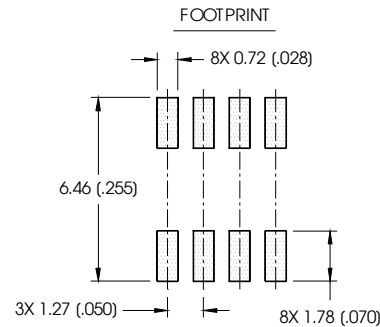
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

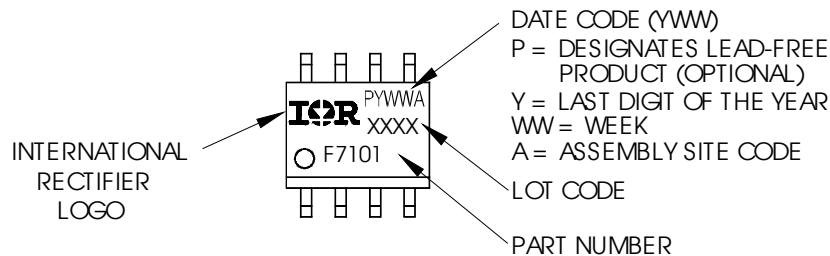


- NOTES:
- DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 - CONTROLLING DIMENSION: MILLIMETER
 - DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 - OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
 - $\textcircled{5}$ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
 - $\textcircled{6}$ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
 - $\textcircled{7}$ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

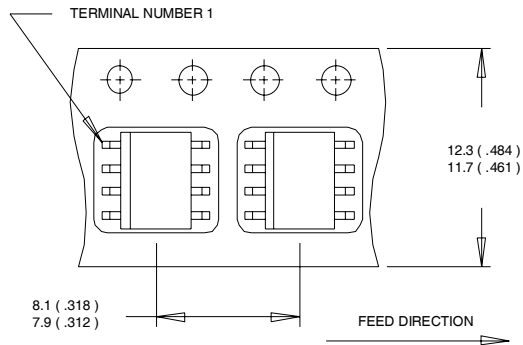


Notes:

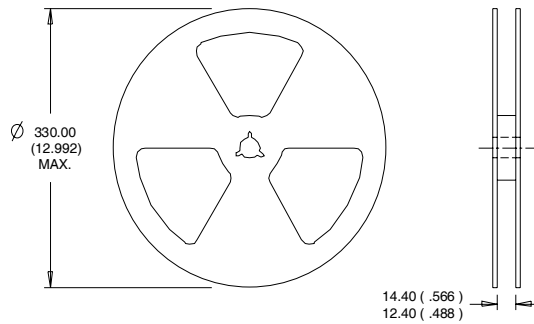
- For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/auto/>
- For the most current drawing please refer to IR website at <http://www.irf.com/package/>

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.